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High-Power Epitaxial GaAs Tunnel Diodes. (E) A. T. Gorelenok, A. N. Imenkov, and B. V. Tsarenkov. 2, 1287 (1969) [2, 1542 (1968)]

Zinc-Compensated Silicon Diodes with Negative Resistance. (E) A. A. Lebedev and N. A. Sultanov. 2, 1295 (1969) [2, 1551 (1968)]

Effect of Inhomogeneities in Silicon on the Energy Resolution of Lithium-Drifted β Spectrometers. (E) N. P. Afanas'eva, S. R. Novikov, N. B. Strokan, and N. I. Tisnek. 2, 1506 (1969) [2, 1809 (1968)]

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15. EXPERIMENT METHODS

Determination of Trap Parameters by a Thermally Stimulated Capacitor Discharge Method. (E/T) A. G. Zhdan, V. B. Sandomirskii, and A. D. Ozheredov. 2, 7 (1968) [2, 11 (1968)]

Determination of the Diffusion Coefficient of Impurities in Piezoelectric Semiconducting Materials. (E) V. S. Vasil'ev and I. N. Kanevskii. 2, 312 (1968) [2, 377 (1968)]

Measurement of the Impurity Concentration in Degenerate Crystals Using the Burstein Effect. (E) O. V. Kosogov and M. A. Maramzina. 2, 854 (1969) [2, 1026 (1968)]

Use of a Laser in Measurements of the Diffusion Length in Epitaxial Films. (E) Yu. A. Kontsevoi and R. R. Rezvyi. 2, 880 (1969) [2, 1050 (1968)]

Photoluminescence Method of Measuring the Equilibrium Carrier Distribution in GaAs. (E) A. T. Gorelenok, B. V. Korobitsyn, B. V. Tsarenkov, and N. G. Chiabrishvili. 2, 1267 (1969) [2, 1518 (1968)]

Investigation of the Cathodoluminescence of Gallium Antimonide Using a Scanning Electron Microscope with a Modulated Beam. (E) G. V. Spivak, G. V. Saparin, M. K. Antoshin, V. M. Stuchebnikov, and A. É. Yunovich. 2, 1492 (1969) [2, 1791 (1968)]

Measurement of the Diffusion Coefficient of Copper in Gallium Arsenide by an Ultrasonic Method. (E) V. S. Vasil'ev, I. N. Kanevskii, and V. B. Osvenskii. 2, 1495 (1969) [2, 1795 (1968)]

ERRATA

To the Author Index for Vol. 1, 1967 ["Soviet Physics – Semiconductors", Vol. 1, No. 12, right-hand column on p. 1556, June, 1968].

The second entry (line 4) under BARYSHEV, N. S. should read "Photoelectric Properties of Mercury Telluride" and not "... Lead Telluride".

To the Subject Index for Vol. 1, 1967 ["Soviet Physics – Semiconductors", Vol. 1, No. 12, left-hand column on p. 1589, June, 1968].

Insert the following entry between lines 9 and 10 from top:

Photoelectric Properties of Lead Telluride. (E)
N. S. Baryshev. 1, 223 (1967) [1, 281 (1967)].